

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE

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ABSTRACT OF THE DISCLOSURE

10 The resist film is provided on the surface of the
substrate having electrodes, and openings are provided in
the resist film at positions of the electrodes on the
substrate. The first metal is supplied into the
openings. The first metal is then heated to melt and
coagulate it. The second metal is then supplied into the
openings on the first metal. The first metal and the
15 second metal are heated to melt and coagulate them. The
resist film is finally removed. By this method,
excellent solder bumps can be formed on the substrate
without remnants of the resist film being left on the
substrate.